

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (currently amended). A circuit device (1), with comprising at least one a first connection (3a) and a second connection (3b), to which a clock pulse (whereby a single clock pulse (CLK, CLK_T) can be applied to the first connection (3a) or a differential clock pulse (CLK, CLK_T, /CLK, /CLK_T) can be applied to the first and second connections (3a, 3b), characterized in that the circuit device (1) also comprises and a clock pulse detection facility (2) to determine detect whether there is a differential clock pulse (CLK, CLK_T, /CLK, /CLK_T) present at the connection (3b) first and second connections (3a, 3b) or a single clock pulse (CLK, CLK_T) present at the first connection (3a).

2 (currently amended). A circuit device (1) with comprising at least one further a first connection (3a), to which a further clock pulse (CLK, CLK_T) can be applied, and a second connection (3b), to which a clock pulse (/CLK, /CLK_T) can be applied, whereby and a detection facility (2) which in determining whether a clock pulse (/CLK, /CLK_T) is present at the second connection (3b), it is determined determines whether there are differential clock pulses (CLK, CLK_T; /CLK, /CLK_T) present at the connections (3a, 3b), or whether there is a single clock pulse (CLK, CLK_T) present at the further first connection (3a), but not at the second connection (3b).

3 (previously presented). A circuit device (1) according to Claim 2, which comprises a comparison device (24) for comparing the signal present at the connection (3b), in particular the clock pulse (/CLK, /CLK_T) applied thereto, with a reference signal (VREF).

4 (original). A circuit device (1) according to claim 3, in which the comparison device (24) comprises a differential amplifier.

5 (previously presented). A circuit device (1) according to Claim 3, in which the comparison device (24) emits a pulse, more specifically a clock pulse detection signal, when the level of the signal present at the connection (3b) exceeds or falls below a predetermined level (VREF), in particular, the level of the reference signal (VREF).

6 (previously presented). A circuit device (1) according to Claim 3, in which the comparison device (24) emits a signal, more specifically a clock pulse detection signal, when the level of the signal present at the connection (3b) first exceeds a predetermined, first level (VREF + ΔU₁), and then falls below a predetermined second level (VREF - ΔU₂) that differs from the first level.

7 (previously presented). A circuit device (1) according to Claim 3, in which the comparison device (24) then emits a pulse, more specifically a clock pulse detection signal, when the level of the signal present at the connection (3b) first falls below a predetermined first level and then exceeds a predetermined second level that differs from the first level.

8 (currently amended). A circuit device (1) according to Claim [[2]] 3, which also comprises a counter device (7), in particular for detecting the number of pulse, particularly clock pulse detection signals, emitted by the comparison device (24).

9 (currently amended). A circuit device (1) according to Claim 8, in which, when the number (Z) of pulse, in particular clock pulse detection signals emitted by the comparison device (24), and detected by the counter device (7), is larger than or equal to a predetermined number (Z₀), it is determined that [[a]] the clock pulse (/CLK, /CLK_T) is present at the connection (3b).

10 (currently amended). A semi-conductor component that comprises at least one circuit device (1) ~~according to Claim 2 comprising:~~

at least a first connection (3a), to which a clock pulse (CLK, CLK_T) can be applied, and a second connection (3b), to which a clock pulse (/CLK, /CLK_T) can be applied; and

a detection facility (2) which in determining whether a clock pulse (/CLK, /CLK_T) is present at the second connection (3b), determines whether there are differential clock pulses (CLK, CLK_T; /CLK, /CLK_T) present at the connections (3a, 3b), or whether there is a single clock pulse (CLK, CLK_T) present at the first connection (3a), but not at the second connection (3b).

11 (original). A semi-conductor component according to Claim 10, which is a DDR (double data rate) component, in particular a DDR memory component.

12 (original). A semi-conductor component according to Claim 10, in which the memory component is a DRAM (dynamic random access memory).